

650V 1.2Ω Zener-protected Power MOSFET

Description

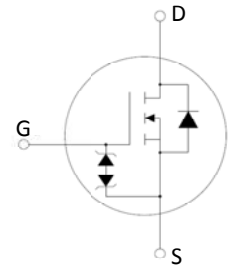
WMOS™ MM is Wayon's new generation super junction MOSFET family that is utilizing charge balance technology for extremely low on-resistance and low gate charge performance. WMOS™ MM is suitable for applications which require superior power density and outstanding efficiency.

Features

- $V_{DS} = 700V @ T_{j,max}$
- Typ. $R_{DS(on)} = 1.2\Omega$
- Ultra low gate charge (Typ. $Q_g = 5.3nC$)
- Zener-protected

Application

LED Lighting, Charger, Adapter, PC, LCD TV



Absolute Maximum Ratings

Parameter	Symbol	WMF05N65MM	Unit
Drain-Source Voltage	V_{DSS}	650	V
Continuous drain current ¹⁾ ($T_C = 25^\circ C$)	I_D	5.4	A
($T_C = 100^\circ C$)		3.2	A
Pulsed drain current ²⁾	I_{DM}	8.8	A
Gate-Source voltage	V_{GSS}	± 30	V
Avalanche energy, single pulse ³⁾	E_{AS}	35	mJ
Avalanche energy, repetitive	E_{AR}	0.1	mJ
Avalanche current, repetitive	I_{AR}	0.6	A
Power Dissipation ($T_C = 25^\circ C$)	P_D	5	W
- Derate above $25^\circ C$		0.04	W/ $^\circ C$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ C$
Continuous diode forward current ¹⁾	I_S	5.4	A
Diode pulse current ²⁾	$I_{S,pulse}$	8.8	A

Thermal Characteristics

Parameter	Symbol	WMF05N65MM	Unit
Thermal Resistance, Junction-to-Solder point	$R_{\theta JS}$	24	$^\circ C/W$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	75	$^\circ C/W$

Electrical Characteristics $T_c = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0 V, I _D =1 mA	650	-	-	V
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =0.25mA	2.5	3.5	4.5	V
Drain cut-off current	I _{DSS}	V _{DS} =650 V, V _{GS} =0 V, T _J = 25°C T _J = 125°C	- -	- 80	1 -	μA
Gate leakage current, Forward	I _{GSSF}	V _{GS} =20 V, V _{DS} =0 V	-	-	1	μA
Gate leakage current, Reverse	I _{GSSR}	V _{GS} =-20 V, V _{DS} =0 V	-	-	-1	μA
Drain-source on-state resistance	R _{DS(on)}	V _{GS} =10 V, I _D =0.8A T _J = 25°C	- -	 1.2	 1.55	 Ω
Dynamic characteristics						
Input capacitance	C _{iss}	V _{DS} = 100 V, V _{GS} = 0 V, f = 1 MHz	-	227	-	pF
Output capacitance	C _{Oss}		-	11	-	
Reverse transfer capacitance	C _{rss}		-	0.9	-	
Turn-on delay time	t _{d(on)}	V _{DD} = 300V, I _D = 2A R _G = 25Ω, V _{GS} =10V	-	8	-	ns
Rise time	t _r		-	23	-	
Turn-off delay time	t _{d(off)}		-	49	-	
Fall time	t _f		-	18	-	
Gate charge characteristics						
Gate to source charge	Q _{gs}	V _{DD} =480 V, I _D =2A, V _{GS} =0 to 10 V	-	1.3	-	nC
Gate to drain charge	Q _{gd}		-	2.1	-	
Gate charge total	Q _g		-	5.3	-	
Gate plateau voltage	V _{plateau}		-	5	-	V
Reverse diode characteristics						
Diode forward voltage	V _{SD}	V _{GS} =0 V, I _F =1A	-	-	1.2	V
Reverse recovery time	t _{rr}	V _R =50 V, I _F =2A, dI _F /dt=100 A/μs	-	135	-	ns
Reverse recovery charge	Q _{rr}		-	0.65	-	μC
Peak reverse recovery current	I _{rrm}		-	7.5	-	A

Notes:

1. DPAK equivalent. Limited by $T_{J\max}$. Maximum duty cycle $D=0.5$
2. Pulse width t_p limited by $T_{J\max}$
3. $I_{AS}=0.6\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, Starting $T_j=25^\circ\text{C}$

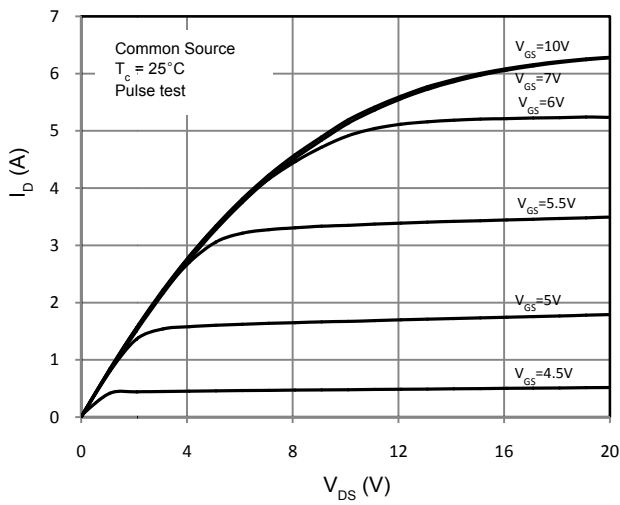


Figure 1. On-Region Characteristics

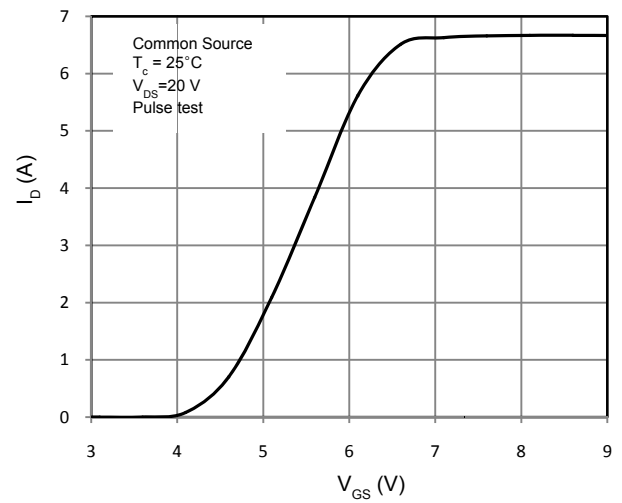


Figure 2. Transfer Characteristics

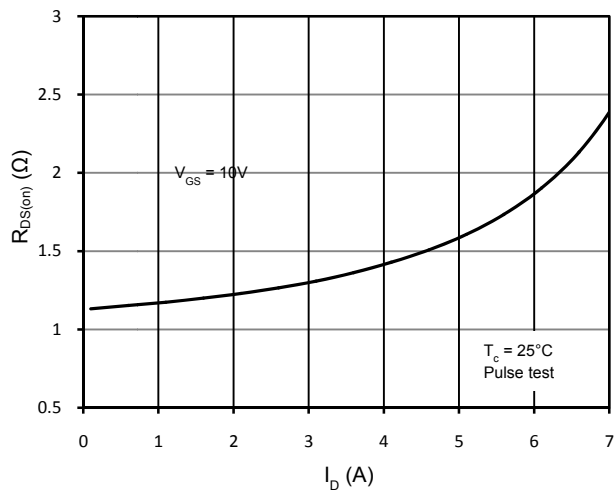


Figure 3. Static Drain-Source On Resistance

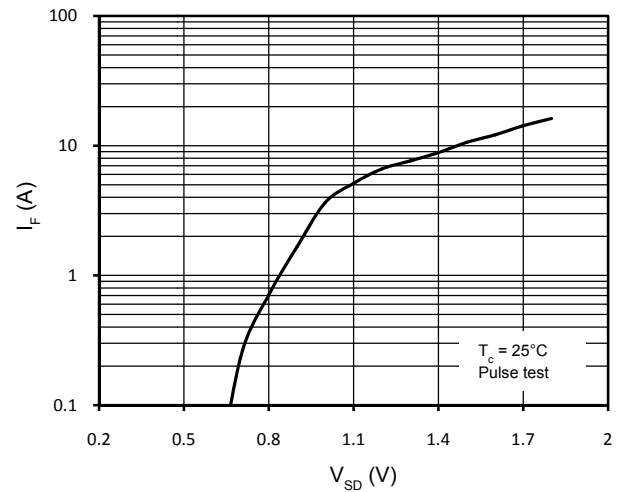
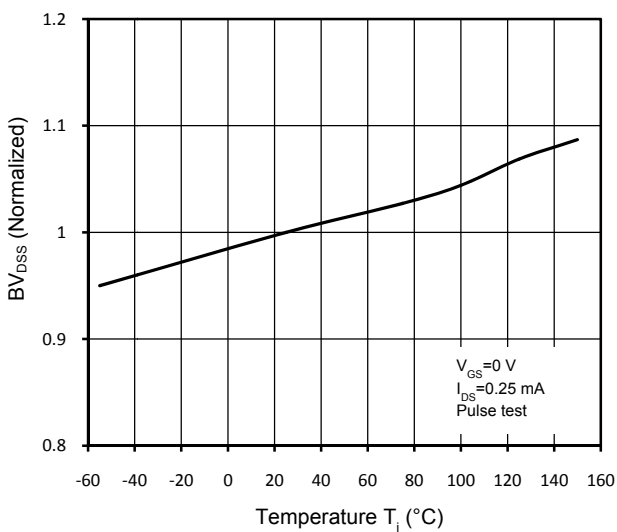
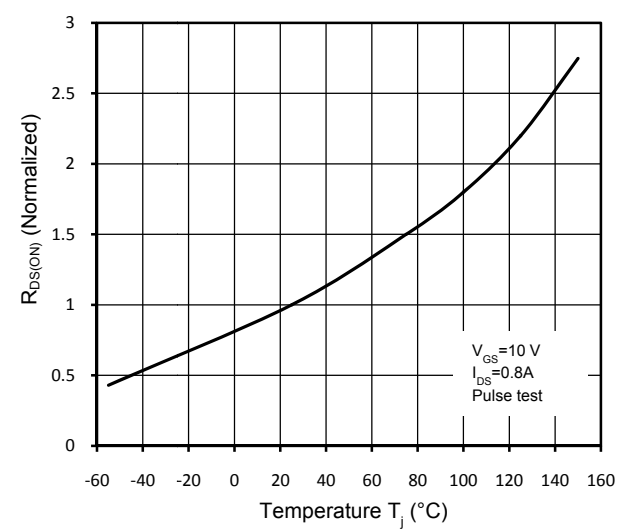


Figure 4. Body-Diode Forward Characteristics

Figure 5. Normalized BV_{DS} vs. TemperatureFigure 6. Normalized $R_{DS(on)}$ vs. Temperature

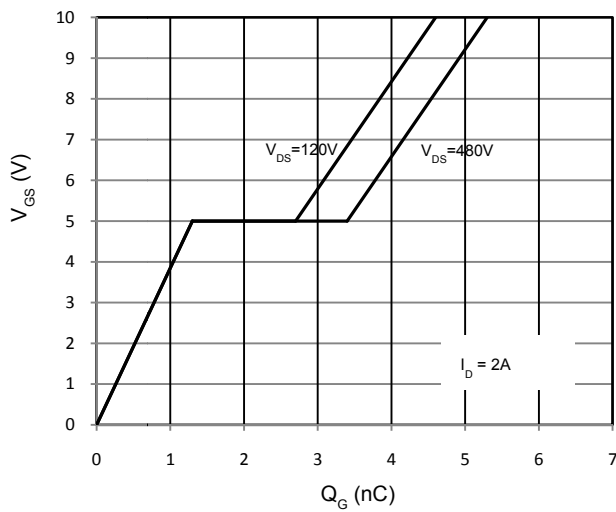


Figure 7. Gate Charge Characteristics

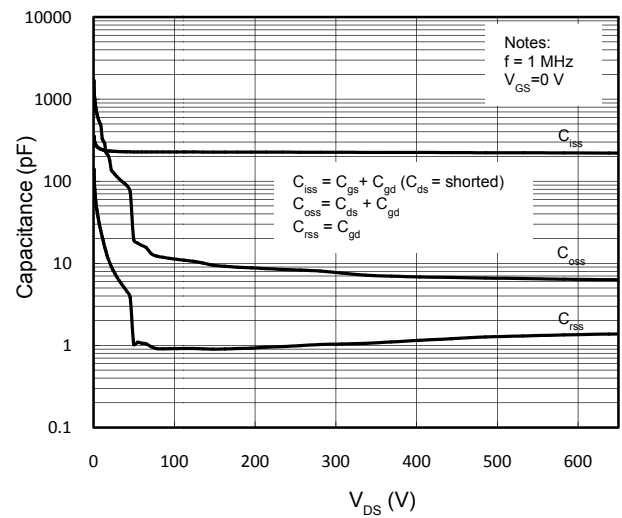


Figure 8. Capacitance Characteristics

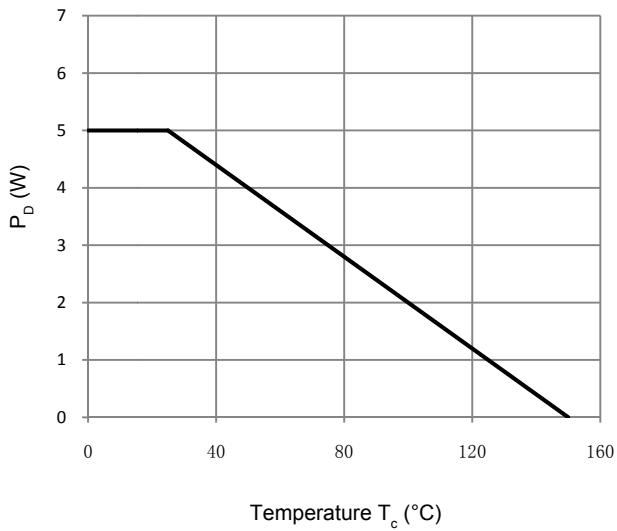


Figure 9. Power Dissipation

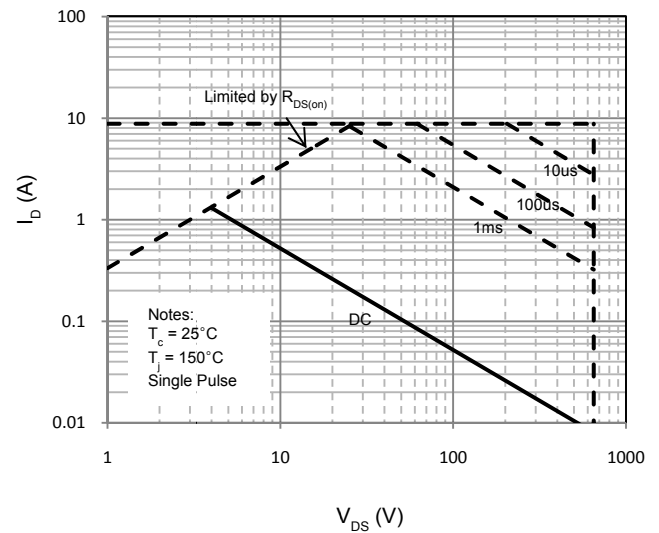


Figure 10. Maximum Safe Operating Area

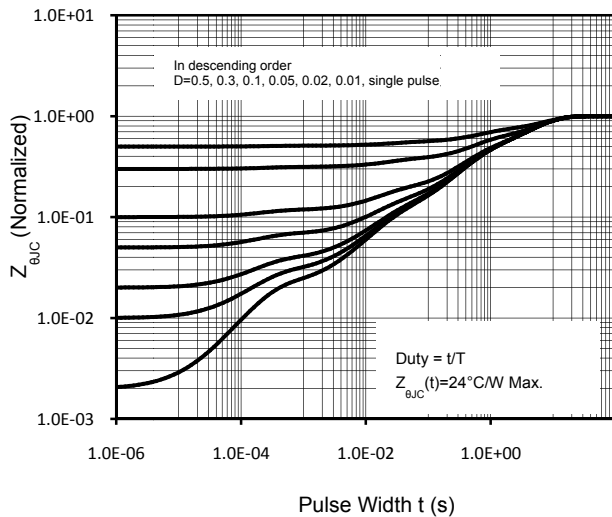
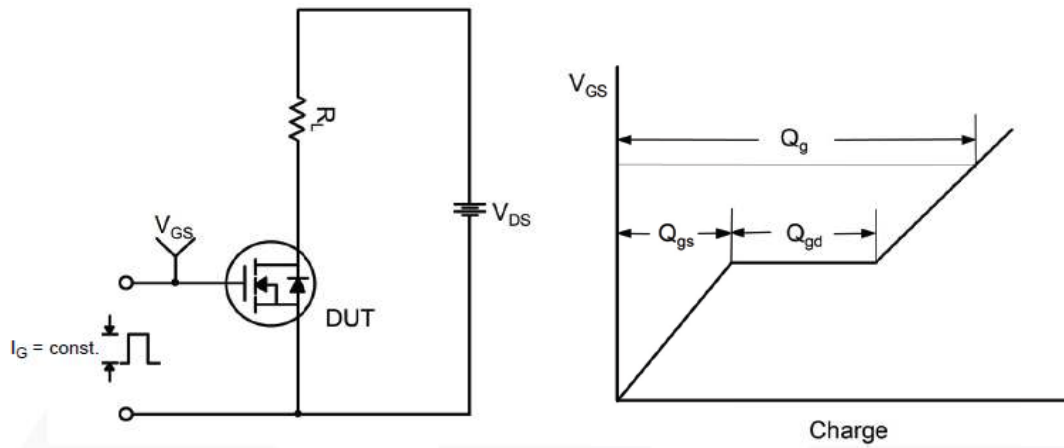
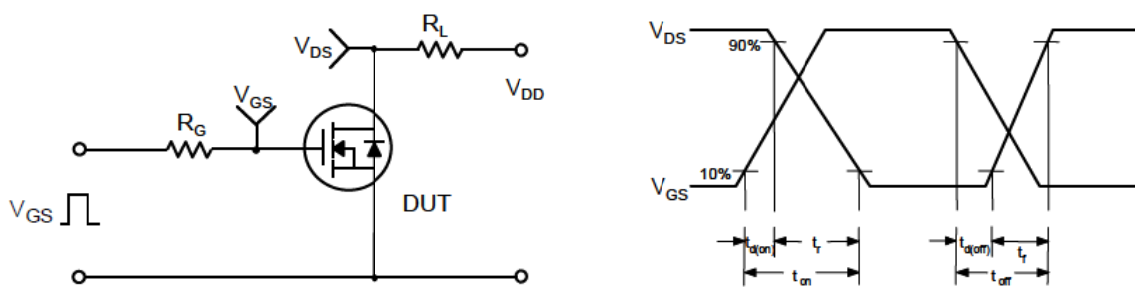


Figure 11. Transient Thermal Response Curve

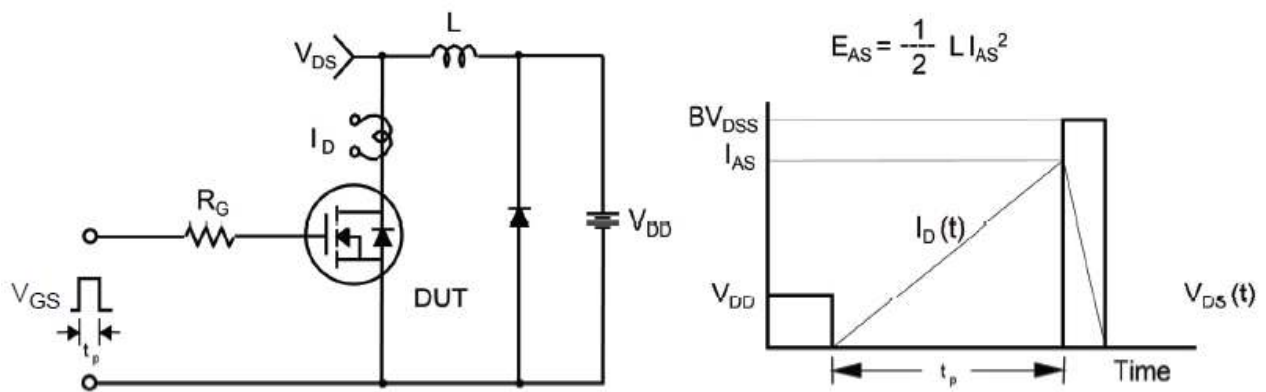
Gate Charge Test Circuit & Waveform



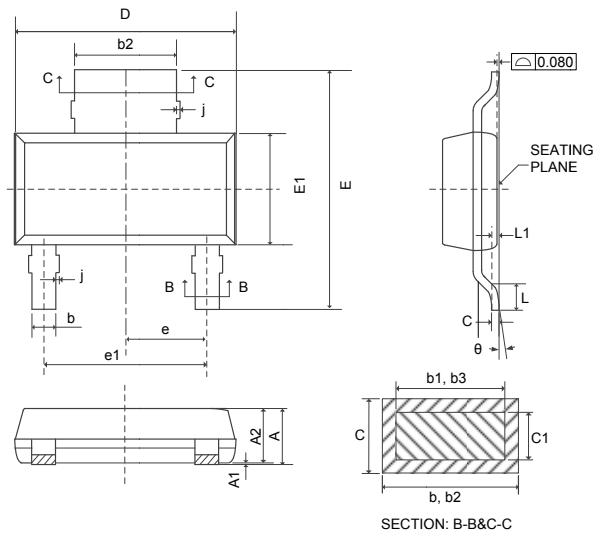
Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions for SOT-223-2L



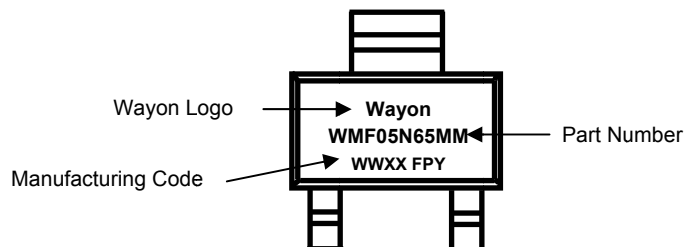
COMMON DIMENSIONS

SYMBOL	mm	
	MIN	MAX
A	-	1.80
A1	0.02	0.10
A2	1.50	1.70
b	0.6	0.84
b1	0.6	0.79
b2	2.90	3.10
b3	2.84	3.05
C	0.23	0.35
C1	0.23	0.33
D	6.30	6.95
E	6.70	7.30
E1	3.30	3.70
e	2.30 BSC	
e1	4.60 BSC	
L	0.81	-
L1	0.25 BSC	
θ	0°	10°
j	-	0.15

Ordering Information

Part	Package	Marking	Packing method
WMF05N65MM	SOT-223-2L	WMF05N65MM	Tape and Reel

Marking Information



Contact Information

No.1001, Shiwan(7) Road, Pudong District, Shanghai, P.R.China.201202

Tel: 86-21-50310888 Fax: 86-21-50757680 Email: market@way-on.com

WAYON website: <http://www.way-on.com>

For additional information, please contact your local Sales Representative.

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